



## Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+NPN)

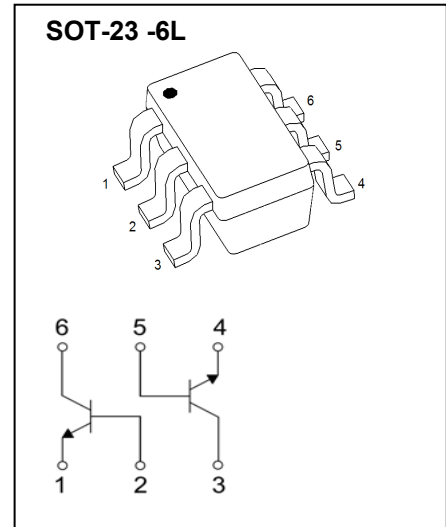
### FEATURE

Complementary PNP Type available MMDT2907AF

**MARKING: K1P**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Units
V <sub>CB0</sub>	Collector-Base Voltage	75	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>c</sub>	Collector Current -Continuous	600	mA
P <sub>c</sub>	Collector Power Dissipation	300	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C



### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

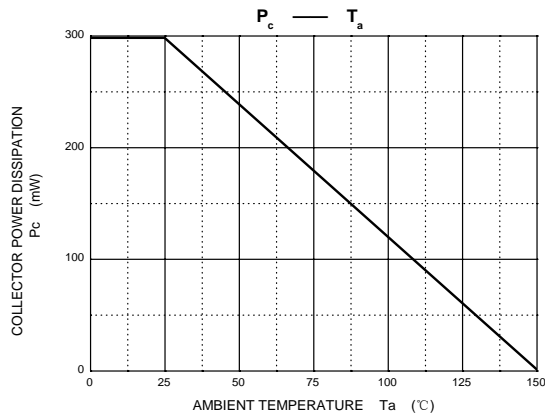
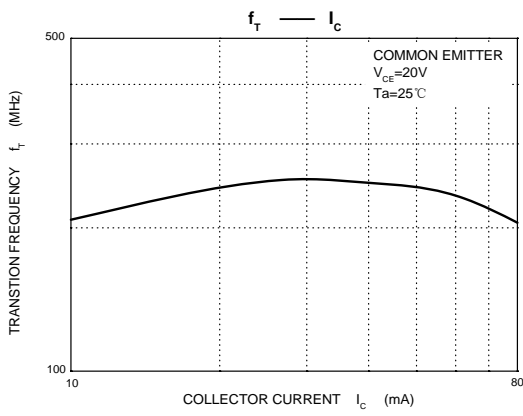
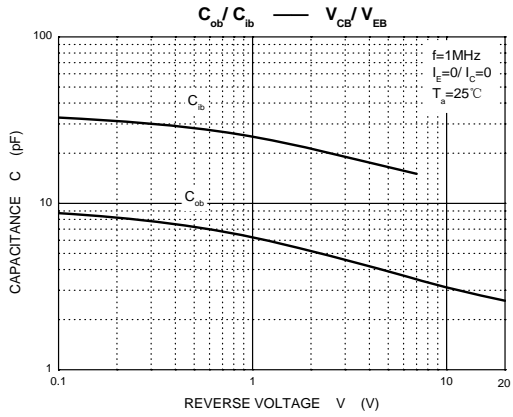
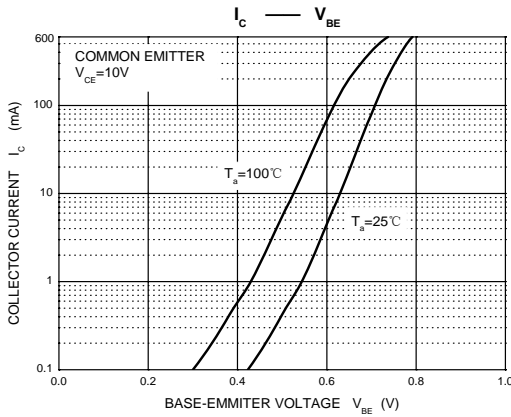
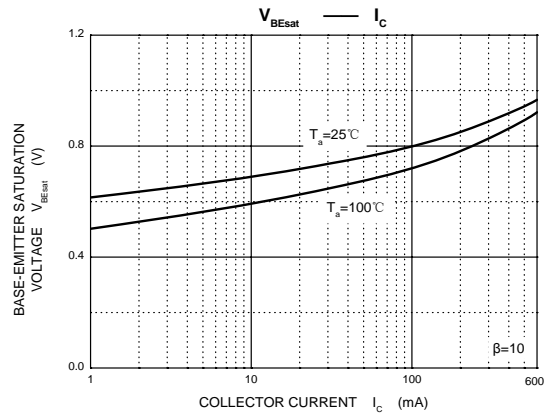
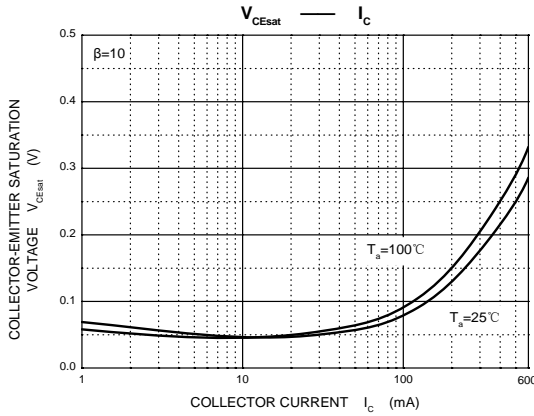
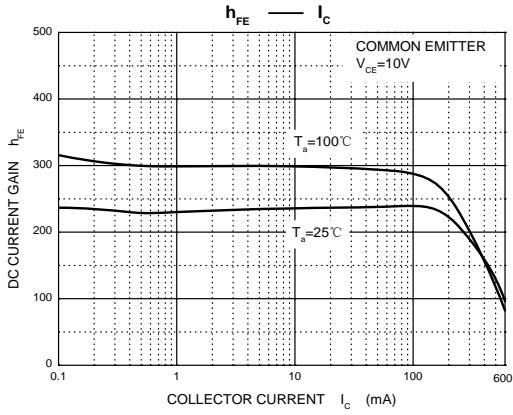
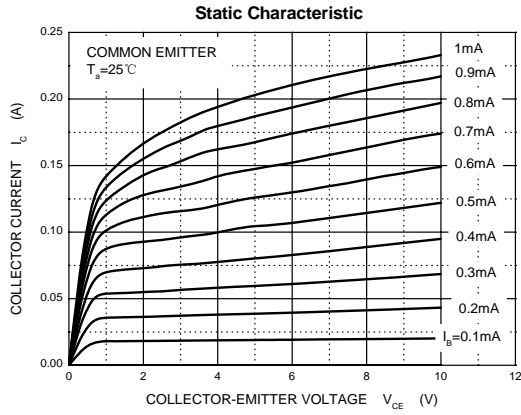
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> =0	75		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	40		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6		V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = 60V, I <sub>E</sub> =0		10	nA
Collector cut-off current	I <sub>CEx</sub>	V <sub>CE</sub> = 60V, V <sub>EB(off)</sub> =3V		10	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 3 V, I <sub>C</sub> =0		10	nA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 0.1mA	35		
	h <sub>FE(2)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 1mA	50		
	h <sub>FE(3)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 10mA	75		
	h <sub>FE(4)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 150mA	100	300	
	h <sub>FE(5)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> = 500mA	40		
	h <sub>FE(6)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> = 150mA	35		
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> = 15mA		0.3	V
	V <sub>CE(sat)2</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> = 50mA		1	V
Base-emitter saturation voltage	V <sub>BE(sat)1</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA	0.6	1.2	V
	V <sub>BE(sat)2</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> = 50mA		2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> = 20mA, f=100MHz	300		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		8	pF
Input Capacitance	C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> = 0, f=1MHz		25	pF
Noise Figure	NF	V <sub>CE</sub> =10V, I <sub>C</sub> =100μA, f=1KHz, R <sub>S</sub> =1KΩ		4	dB

### Switching characteristics

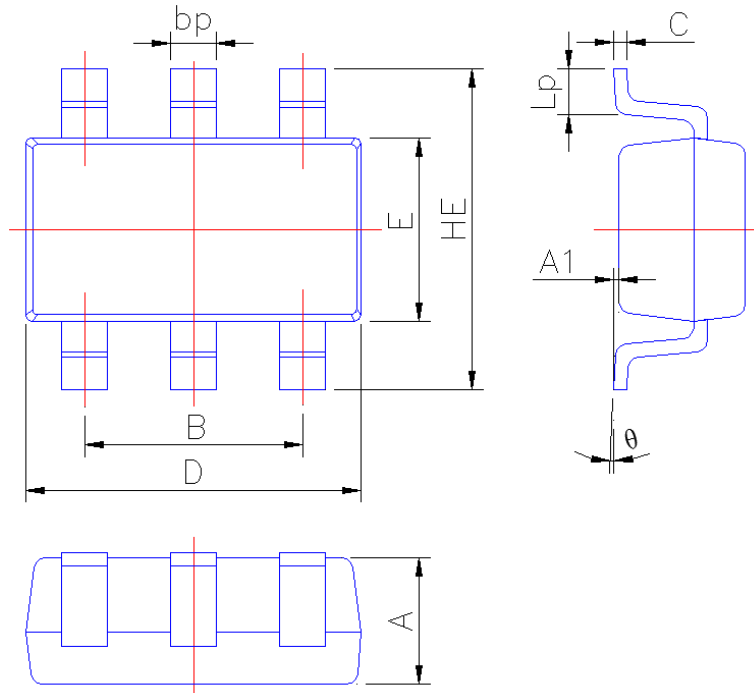
Parameter	Symbol	Test conditions	Min	Max	Unit
Delay time	t <sub>d</sub>	V <sub>CC</sub> =30V, I <sub>C</sub> =150mA,		10	nS
Rise time	t <sub>r</sub>	V <sub>BE(off)</sub> =0.5V, I <sub>B1</sub> =15mA		25	nS
Storage time	t <sub>s</sub>	V <sub>CC</sub> =30V, I <sub>C</sub> =150mA,		225	nS
Fall time	t <sub>f</sub>	I <sub>B1</sub> = -I <sub>B2</sub> = 15mA		60	nS



Typical Characteristics



## SOT-23-6L Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	1.05	1.20
A1	0.010	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.15
D	2.80	3.00
E	1.50	1.70
HE	2.60	3.00
Lp	0.25	0.55
$\theta$	2°	6°